SOI SUBSTRATE AND MANUFACTURING METHOD THEREOF

ABSTRACT OF THE DISCLOSURE

The semiconductor substrate provided with a groove portion is irradiated with ions so that an embrittled region is formed in the semiconductor substrate, the semiconductor substrate and a base substrate are bonded to each other with an insulating layer interposed therebetween and a space which is surrounded by the groove portion in the semiconductor substrate and the base substrate is formed, and heat treatment is performed to separate the semiconductor substrate at the embrittled region, so that the semiconductor layer is formed over the base substrate with the insulating layer interposed therebetween.

Figure 1